Stanislaw Kochowski

List of Publications by Year
in descending order

24	342	1040056 9	794594 19
papers	citations	h-index	g-index

24	24	24	314
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Bilayer structure for hydrogen detection in a surface acoustic wave sensor system. Sensors and Actuators B: Chemical, 2002, 82, 265-271.	7.8	116
2	Description of the frequency behaviour of metalâ€“SiO2â€“GaAs structure characteristics by electrical equivalent circuit with constant phase element. Thin Solid Films, 2002, 415, 133-137.	1.8	58
3	Concentration and mobility of charge carriers in thin polycrystalline films of bismuth. Thin Solid Films, 1978, 48, 345-351.	1.8	45
4	Some effects of (NH4)2Sx treatment of n-GaAs surface on electrical characteristics of metal-SiO2â€“GaAs structures. Vacuum, 2000, 57, 157-162.	3.5	20
5	Investigation of sensor properties of copper phthalocyanine with the use of surface acoustic waves. Sensors and Actuators B: Chemical, 1994, 22, 133-137.	7.8	18
6	Two constant phase element behaviour of the admittance characteristics of GaAs metal-insulator-semiconductor structure with deep traps. Thin Solid Films, 2003, 444, 208-214.	1.8	15
7	Some electrical properties and structural investigations of thin bismuth films evaporated in a high vacuum. Thin Solid Films, 1973, 17, 199-205.	1.8	11
8	Electrical properties of SiO 2 â€“(n) GaAs interface on the basis of measurements of MIS structure capacitance and conductance. Thin Solid Films, 1999, 348, 180-187.	1.8	11
9	Photodeflection signal formation in photothermal measurements: comparison of the complex ray theory, the ray theory, the wave theory, and experimental results. Applied Optics, 2007, 46, 5216.	2.1	10
10	Electronic properties of the iron phthalocyanine thin films UHV annealed and exposed to oxygen. Vacuum, 1995, 46, 547-549.	3.5	8
11	Electronic properties of the space charge layer of the copper phthalocyanine thin films. European Physical Journal D, 1993, 43, 1041-1044.	0.4	6
12	Photoemission yield spectroscopy investigations of the electronic properties of copper phtalocyanine thin films UHV annealed and exposed to oxygen. Physica Status Solidi (B): Basic Research, 1994, 183, K9.	1.5	6
13	Studies of GaAs metalâ€“insulatorâ€“semiconductor structures by the admittance spectroscopy method. Applied Surface Science, 2004, 235, 389-394.	6.1	6
14	Characterization of the interface and the bulk phenomena in metalâ€“SiO2â€“(n) GaAs structure by analysis of the equivalent circuit parameters at different temperatures. Thin Solid Films, 2004, 467, 190-196.	1.8	5
15	The contribution of surface effects to the surface photovoltage dependence on temperature for the real Si(111) surface. Surface Science, 1988, 200, 172-178.	1.9	3
16	An anomalous dependence of the specific resistance on thickness for thin films of Bi in the temperature range 78 â€“ 293 K. Thin Solid Films, 1975, 28, L35-L37.	1.8	1
17	Investigations by the surface photo-E.M.F. method of the effect of low temperature vacuum baking of an Si(111) surface. Thin Solid Films, 1982, 88, 381-384.	1.8	1
18	An analysis of small-signal response of the SiO2â€“(n) GaAs interface based on a surface disorder model. Vacuum, 1999, 54, 183-188.	3.5	1

#	Article	IF	Citations
19	Analysis of MIS equivalent electrical circuit of Au/Pd/Ti-SiO2-GaAs structure based on DLTS measurements. Materials Science-Poland, 2013, 31, 446-453.	1.0	1
20	Gaussian optical beam propagation in thermal wave field â€“ the ray theory, the complex ray theory and experimental results. European Physical Journal Special Topics, 2005, 129, 231-236.	0.2	0
21	Experimental verification of theory of photodeflection detection based on complex geometrical optics. European Physical Journal Special Topics, 2006, 137, 305-308.	0.2	0
22	Charge transient spectroscopy measurements of GaAs metalâ€“insulatorâ€“semiconductor structures. Applied Surface Science, 2006, 252, 7631-7635.	6.1	0
23	The analysis of filling pulse parameters influence on ICTS data of GaAs MIS structures. Proceedings of SPIE, 2013, , .	0.8	0
24	Description of Electrical Characteristics of Semiconducting Compound-Insulator Interface on the Basis of the Model of Interface States Distributed in Energy and in Space. Acta Physica Polonica A, 1992, 82, 761-764.	0.5	0